



SIR862DP-T1-GE3 Information



For Reference Only

Part Number SIR862DP-T1-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 25V 50A PPAK SO-8

Package PowerPAK? SO-8

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SIR862DP-T1-GE3 Specifications

Manufacturer Part Number SIR862DP-T1-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package PowerPAK? SO-8 Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 25V Current - Continuous Drain (Id) @ 25°C 50A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 90nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3800pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 69W (Tc) Rds On (Max) @ Id, Vgs 2.8 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8		
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Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 25V Current - Continuous Drain (Id) @ 25°C 50A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 90nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3800pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 69W (Tc) Rds On (Max) @ Id, Vgs 2.8 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As Don (Max) @ Id, Vgs Current - Continuous Drain (Id) @ 25°C SOA (Tc) 50A (Tc) 50B (T0V 50B (T0V 50B (TC) 50B (TC)	Package	PowerPAK? SO-8
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)25VCurrent - Continuous Drain (Id) @ 25°C50A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs90nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3800pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 69W (Tc)Rds On (Max) @ Id, Vgs2.8 mOhm @ 15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8	Series	TrenchFET?
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Case On (Max) @ Id, Vgs Derating Temperature Supplier Device Package PowerPAK? SO-8 Package / Case Sun (Max On, Min Rds On) 4.5V, 10V 2.3V @ 250μA 3800pF @ 10V 3800pF @ 10V 5.2W (Ta), 69W (Tc) 2.8 mOhm @ 15A, 10V -55°C ~ 150°C (TJ) Surface Mount PowerPAK? SO-8	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs90nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3800pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 69W (Tc)Rds On (Max) @ Id, Vgs2.8 mOhm @ 15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8	Drain to Source Voltage (Vdss)	25V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 PowerPAK? SO-8	Current - Continuous Drain (Id) @ 25°C	50A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) #20V FET Feature Power Dissipation (Max) #38 Mohr @ 10 Mounting Type Surface Mount Supplier Device Package Power PAK? SO-8 Power PAK? SO-8	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.8 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Vgs(th) (Max) @ Id	2.3V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 69W (Tc) Rds On (Max) @ Id, Vgs 2.8 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Gate Charge (Qg) (Max) @ Vgs	90nC @ 10V
FET Feature - Power Dissipation (Max) 5.2W (Ta), 69W (Tc) Rds On (Max) @ Id, Vgs 2.8 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Input Capacitance (Ciss) (Max) @ Vds	3800pF @ 10V
Power Dissipation (Max) 5.2W (Ta), 69W (Tc) 2.8 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs2.8 mOhm @ 15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Power Dissipation (Max)	5.2W (Ta), 69W (Tc)
Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Rds On (Max) @ Id, Vgs	2.8 mOhm @ 15A, 10V
Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case PowerPAK? SO-8	Mounting Type	Surface Mount
č	Supplier Device Package	PowerPAK? SO-8
Report errors?	Package / Case	PowerPAK? SO-8
		Report errors?

SIR862DP-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SIR862DP-T1-GE3 Payment Methods



















SIR862DP-T1-GE3 Shipping Methods













If you have any question about SIR862DP-T1-GE3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com